



High Voltage Trench Schottky Diode

FEATURES

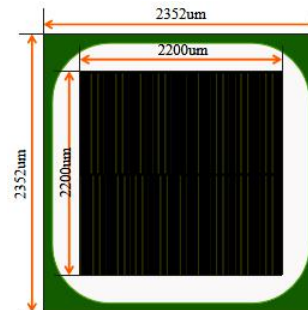
- Trench MOS Schottky technology
- Die in 6" Wafer Form
- 120V, 10A*
- $V_F=0.70V$ (typ.)**

Electrical Characteristics (T_j=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
V _{RRM}	Maximum repetitive peak reverse voltage	125	137	—	V	I _R =500μA
V _F	Static Forward Voltage	—	0.40	0.52	V	I _F =1A
		—	0.56	0.62	V	I _F =5A
		—	0.70	0.76	V	I _F =10A
I _R ***	Cathode-To-Anode Leakage Current	—	9	20	μA	V _R =120V
T _J , T _{STG}	Operating and Storage Temperature Range	-55°C to 150°C Max				
*** Pulse width < 300 uS, Duty cycle < 2%						

Mechanical Data

Parameter	Value	Unit	CHIP DRAWING (Scribe Line is Excluded)
Die Size	2412×2412	μm ²	
Source Pad Size	2200 × 2200	μm ²	
Scribe Line Size	60	μm	
Wafer Diameter	6	in	
Wafer Thickness	250	μm	
Estimated Gross Die	2708(Yield>98%)		
Anode Metal Thickness	AlSiCu(5.5μm)		
Cathode Metal Thickness	Ti\Ni\Ag(0.2μm\0.3μm\2μm)		
Recommended Storage Environment	Store in original container, in dry nitrogen, < 6 months at an ambient temperature of 23°C±3°C >		



* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

** Electrical characteristics are reported for the bare die. Variations in customer packaging materials, dimensions and processes may affect parametric performance.